

Headphone driver for digital audio

BA3578FS / BA3579FS

The BA3578FS and BA3579FS are headphone drivers with internal an LPF and fixed bass boost circuit for multi-bit D / A converters.

●Applications

Portable CD players

●Features

- 1) Suitable for use in digital audio equipment (line-out output noise voltage: $18\mu\text{Vrms}$, S / N = 95dB Typ.).
- 2) Internal LPF for multi-bit D / A converters (fc = 34kHz, -12dB / oct. Typ.).
- 3) Headphone mute function.
- 4) Internal BB (bass boost) circuit.
- 5) Internal supply current for line-mute transistor.
- 6) No need for output oscillation preventive measures.
- 7) Internal standby switch.

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Power supply voltage	AV _{DD}	5.5	V
	PV _{CC}	5.5	V
Power dissipation	Pd	600*1	mW
Operating temperature	Topr	-20~+60	°C
Storage temperature	Tstg	-55~+125	°C

*1 Reduced by 6mW for each increase in Ta of 1°C over 25°C.

●Recommended operating conditions

Parameter	Symbol	Limits	Unit
Power supply voltage	AV _{DD}	3.6	V
	PV _{CC}	3.6	V

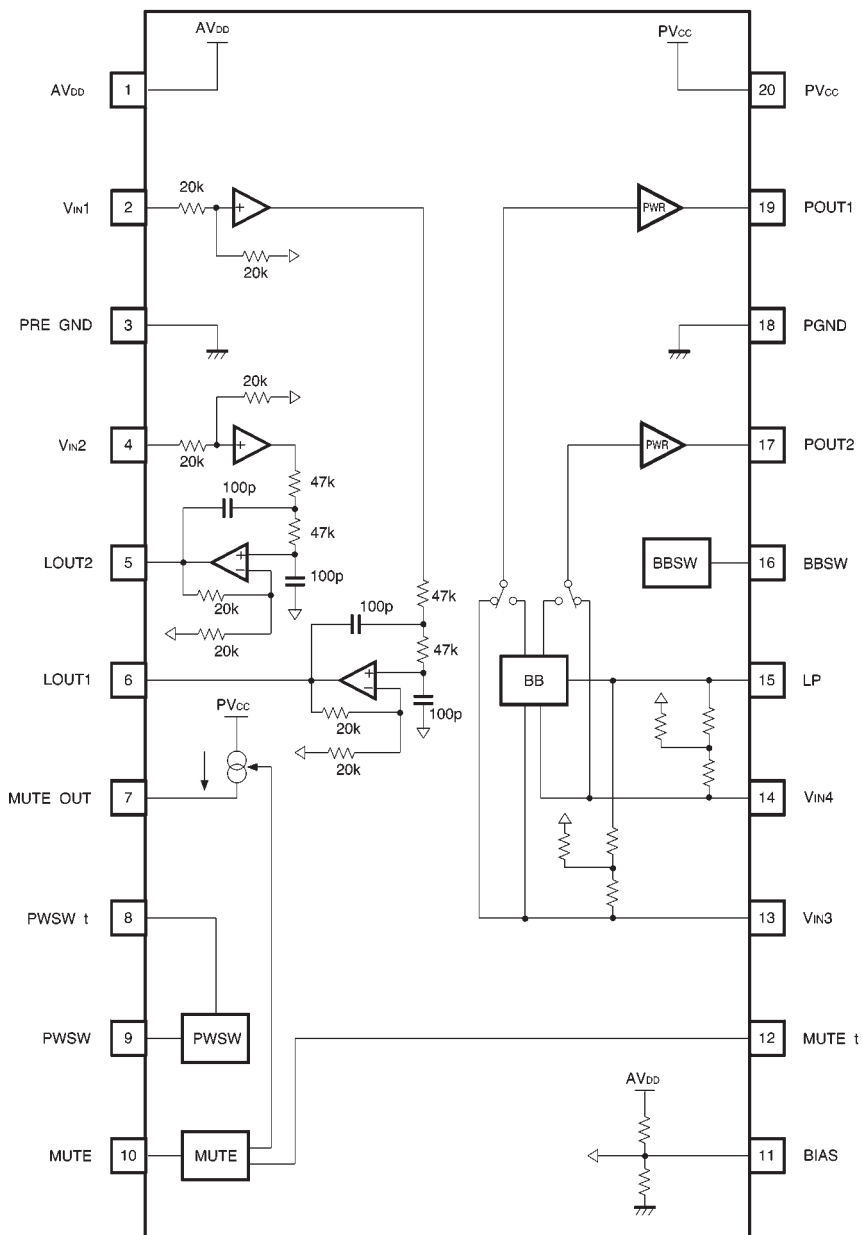
●Recommended operating range

Parameter	Symbol	Limits	Unit
Power supply voltage	AV _{DD}	2.8~5.0	V
	PV _{CC}	2.8~5.0*2	V

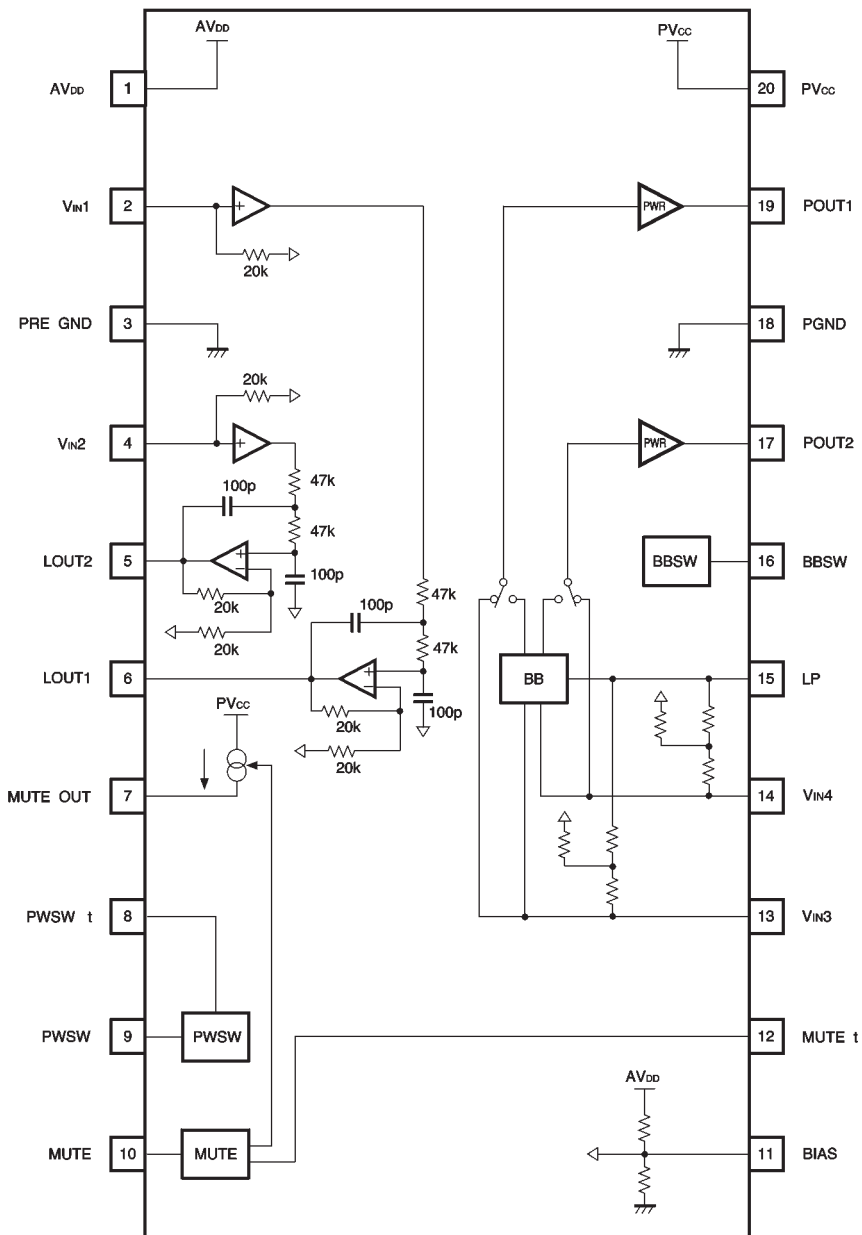
*2 In order to use the headphone output to its optimum performance, have the power supply voltage such that $PV_{CC} \geq AV_{DD} - 0.3V$

● Block diagram

BA3578FS



BA3579FS



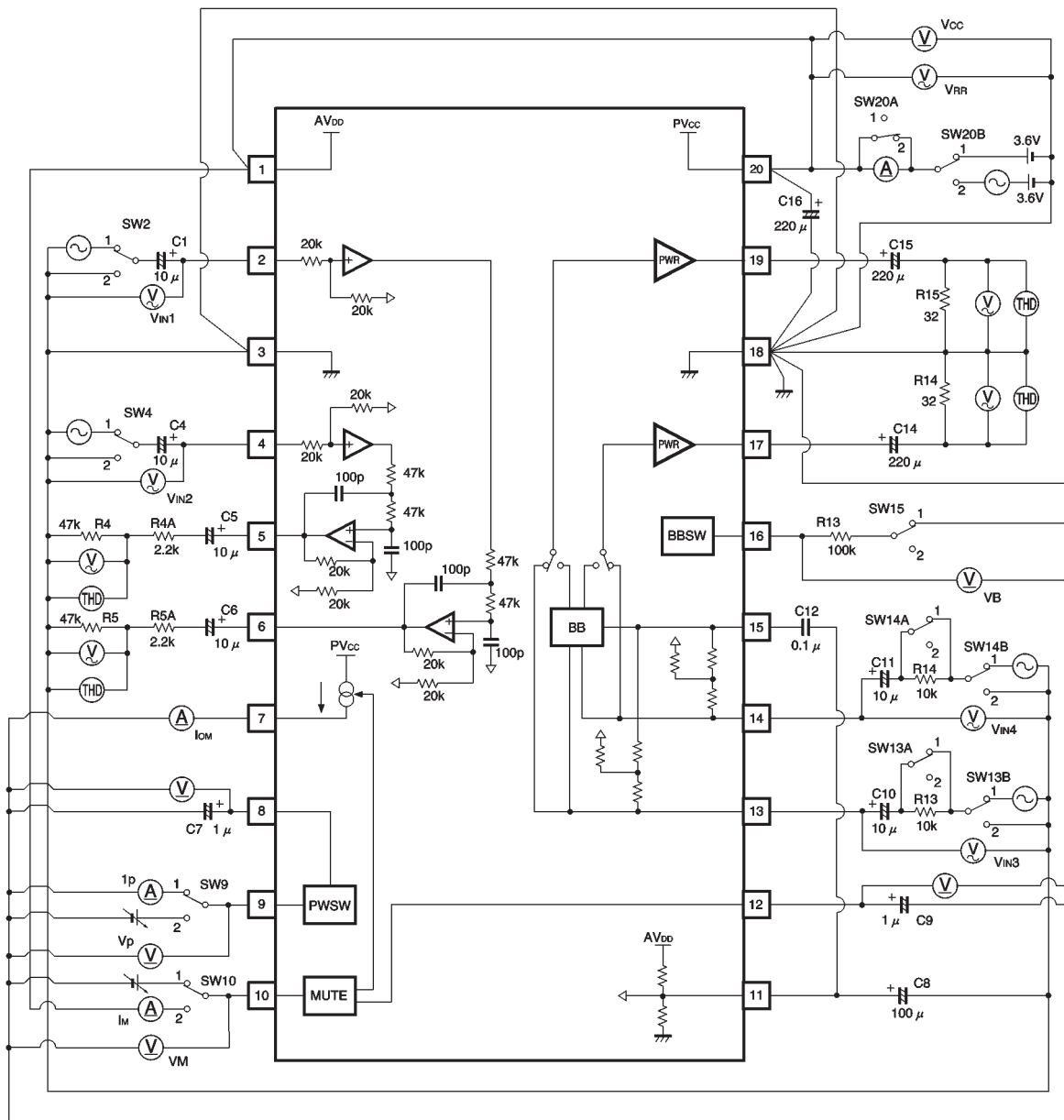
- Electrical characteristics (Unless otherwise noted, $T_a = 25^\circ\text{C}$, $PV_{CC} = AV_{DD} = 3.6\text{V}$, $f = 1\text{kHz}$, $PwSw = \text{ON}$, $MUTE = \text{OFF}$, $BB = \text{OFF}$, Line $R_{L1} = 47\text{k}\Omega$, headphone $R_{L2} = 32\Omega$, filter = DIN AUDIO, line-out measurements are with V_{IN3} and $4 = 0\text{V}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Coniditions
Circuit current	I_{CC}	4.5	7.5	11.5	mA	$V_{IN}=0$
Power ON voltage	V_P	2.0	2.8	—	V	
Power ON pin current	I_P	—	60	110	μA	$V_{PWSW}=0\text{V}$
Mute ON voltage	V_M	—	0.8	1.4	V	
Mute pin current	I_M	—	110	190	μA	$V_{MUTE}=AV_{DD}$
Mute output current	I_{OM}	1.0	2.0	—	mA	$V_{MUTE}=AV_{DD}$
Bass boost OFF voltage	V_B	0.5	0.7	—	V	
〈Line-out〉 (BA3578FS)						
Voltage gain	G_{V1}	−2.4	−0.4	1.6	dB	V_{IN1} , $2=0.8\text{Vrms}$
Voltage gain difference	ΔG_V	−2.1	−0.3	1.2	dB	G_{V1} ($f=1\text{kHz}$) $-G_{V1}$ ($f=10\text{kHz}$)
Total harmonic distortion 1	THD_1	—	0.05	0.2	%	V_{IN1} , $2=0.8\text{Vrms}$
Maximum output voltage 1	V_{OM1}	0.8	1.1	—	Vrms	$THD=0.2\%$
Output noise voltage 1	V_{NO1}	—	−96	−90	dBV	$R_g=0$
Channel separation 1	CS_1	68	78	—	dB	V_{IN1} , $2=0.8\text{Vrms}$, $R_g=0$
Ripple rejection 1	RR_1	37	47	—	dB	$V_{RR}=-20\text{dBV}$, $f_{RR}=1\text{kHz}$, $R_g=0$
〈Line-out〉 (BA3579FS)						
Voltage gain	G_{V1}	3.6	5.6	7.6	dB	V_{IN1} , $2=0.4\text{Vrms}$
Voltage gain difference	ΔG_V	−2.1	−0.3	1.2	dB	G_{V1} ($f=1\text{kHz}$) $-G_{V1}$ ($f=10\text{kHz}$)
Total harmonic distortion 1	THD_1	—	0.05	0.2	%	V_{IN1} , $2=0.4\text{Vrms}$
Maximum output voltage 1	V_{OM1}	0.8	1.1	—	Vrms	$THD=0.2\%$
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Channel separation 1	CS_1	68	78	—	dB	V_{IN1} , $2=0.4\text{Vrms}$, $R_g=0$
Ripple rejection 1	RR_1	37	47	—	dB	$V_{RR}=-20\text{dBV}$, $f_{RR}=1\text{kHz}$, $R_g=0$
〈Headphone out〉						
Voltage gain 2	G_{V2}	10.2	12.2	14.2	dB	V_{IN3} , $4=-20\text{dBV}$
Total harmonic distortion 2	THD_2	—	0.1	0.5	%	V_{IN3} , $4=-20\text{dBV}$
Rated output	P_O	20	32	—	mW	$THD=10\%$
Output noise voltage 2	V_{NO2}	—	−90	−84	dBV	$R_g=0$
Channel separation 2	CS_2	59	69	—	dB	V_{IN3} , $4=-20\text{dBV}$, $R_g=0$
Channel separation 3	CS_3	11	14	—	dB	V_{IN3} , $4=-20\text{dBV}$, $R_g=0$, $BB \text{ ON}$
Channel separation 4	CS_4	25	35	—	dB	V_{IN3} , $4=-20\text{dBV}$, $R_g=10\text{k}\Omega$
Mute attenuation	ATT_M	59	69	—	dB	V_{IN3} , $4=-20\text{dBV}$, $MUTE \text{ ON}$
Bass boost	BB	6.1	9.1	12.1	dB	V_{IN3} , $4=-30\text{dBV}$, $f=100\text{Hz}$, $BB \text{ ON}$
Ripple rejection 2	RR_2	26	36	—	dB	$V_{RR}=-20\text{dBV}$, $f_{RR}=1\text{kHz}$, $R_g=0$

©Not designed for radiation resistance.

● Measurement circuits

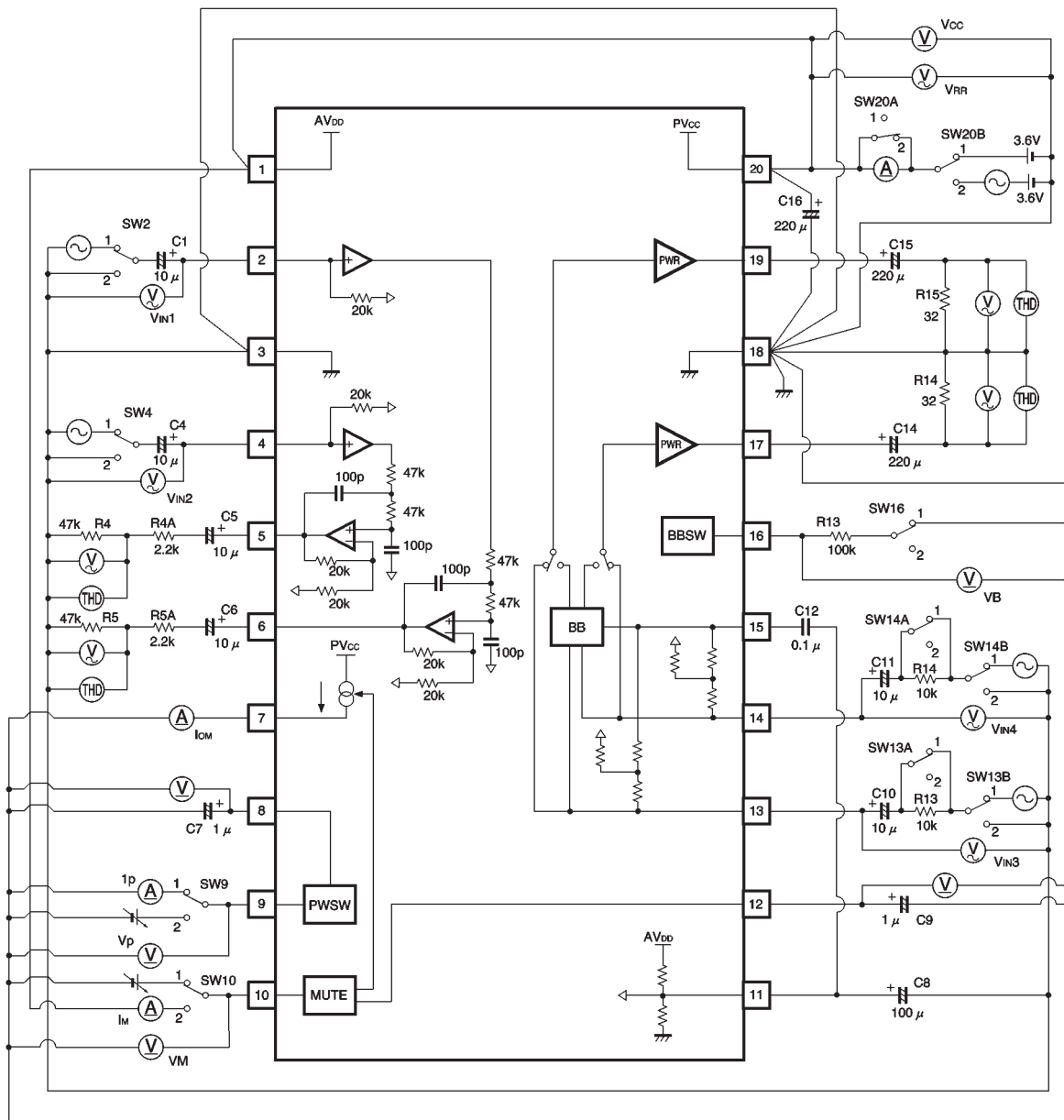
BA3578FS



Units:
 Resistance : Ω ($\pm 1\%$)
 Capacitance (film) : F ($\pm 1\%$)
 Capacitance (electrolytic): F ($\pm 5\%$)

Fig.1

BA3579FS



Units:
 Resistance : Ω ($\pm 1\%$)
 Capacitance (film) : F ($\pm 1\%$)
 Capacitance (electrolytic) : F ($\pm 5\%$)

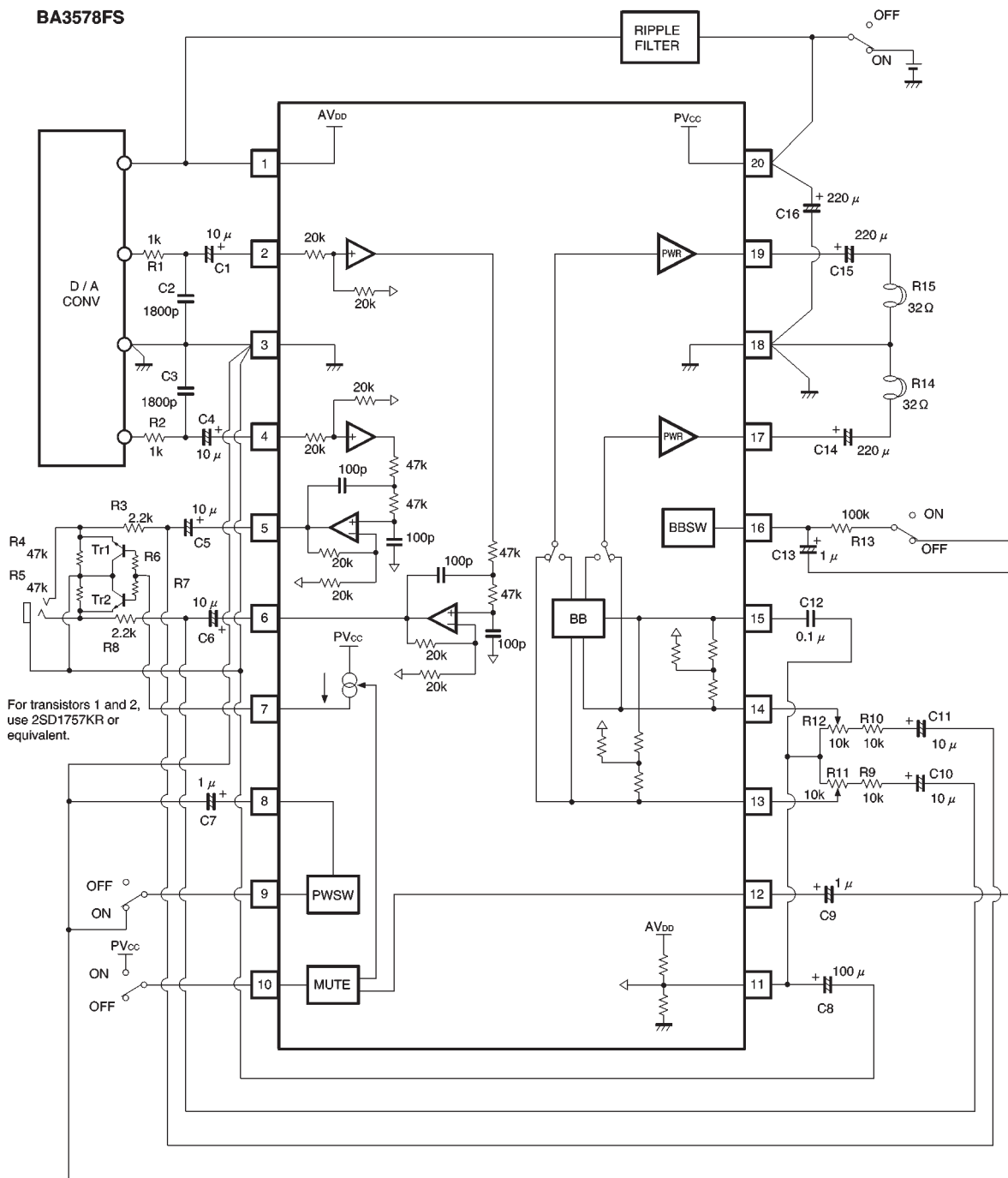
Fig.2

Measurement conditions

Parameter	Symbol	SW2	SW4	SW9	SW10	SW13 A	SW13 B	SW14 A	SW14 B	SW16	SW20 A	SW20 B
Circuit current	I _{CC}	2	2	1	1	1	2	1	2	1	1	1
Power ON voltage	V _P	↓	↓	2	↓	↓	↓	↓	↓	↓	2	↓
Power ON pin current	I _P	↓	↓	1	↓	↓	↓	↓	↓	↓	↓	↓
Mute ON voltage	V _M	↓	↓	↓	2	↓	↓	↓	↓	↓	↓	↓
Mute pin current	I _M	↓	↓	↓	↓	↓	↓	↓	↓	↓	↓	↓
Mute output current	I _{OM}	↓	↓	↓	1	↓	↓	↓	↓	↓	↓	↓
Bass boost OFF voltage	V _B	↓	↓	↓	↓	↓	↓	↓	↓	↓	↓	↓
〈Line-out〉												
Voltage gain 1	G _{V1}	1	1	↓	↓	↓	2	↓	2	↓	↓	↓
Voltage gain difference	ΔG _V	↓	↓	↓	↓	↓	↓	↓	↓	↓	↓	↓
Total harmonic distortion 1	THD ₁	↓	↓	↓	↓	↓	↓	↓	↓	↓	↓	↓
Maximum output voltage 1	V _{OM1}	↓	↓	↓	↓	↓	↓	↓	↓	↓	↓	↓
Output noise voltage 1	V _{NO1}	2	2	↓	↓	↓	↓	↓	↓	↓	↓	↓
Channel separation 1	CS ₁	1 / 2	2 / 1	↓	↓	↓	↓	↓	↓	↓	↓	↓
Ripple rejection 1	RR ₁	2	2	↓	↓	↓	↓	↓	↓	↓	↓	2
〈Headphone out〉												
Voltage gain 2	G _{V2}	2	2	↓	↓	↓	↓	↓	↓	↓	↓	1
Total harmonic distortion 2	THD ₂	↓	↓	↓	↓	↓	↓	↓	↓	↓	↓	↓
Rated output	P _O	↓	↓	↓	↓	↓	↓	↓	↓	↓	↓	↓
Output noise voltage 2	V _{NO2}	↓	↓	↓	↓	↓	2	↓	2	↓	↓	↓
Channel separation 2	CS ₂	↓	↓	↓	↓	↓	1 / 2	↓	2 / 1	↓	↓	↓
Channel separation 3	CS ₃	↓	↓	↓	↓	↓	↓	↓	↓	2	↓	↓
Channel separation 4	CS ₄	↓	↓	↓	↓	2 / 1	↓	1 / 2	↓	1	↓	↓
Mute attenuation	ATT _M	↓	↓	↓	2	1	1	1	1	1	↓	↓
Bass boost	BB	↓	↓	↓	↓	↓	↓	↓	↓	2	↓	↓
Ripple rejection 2	RR ₂	1	↓	↓	↓	↓	2	↓	2	1	↓	2

● Application examples

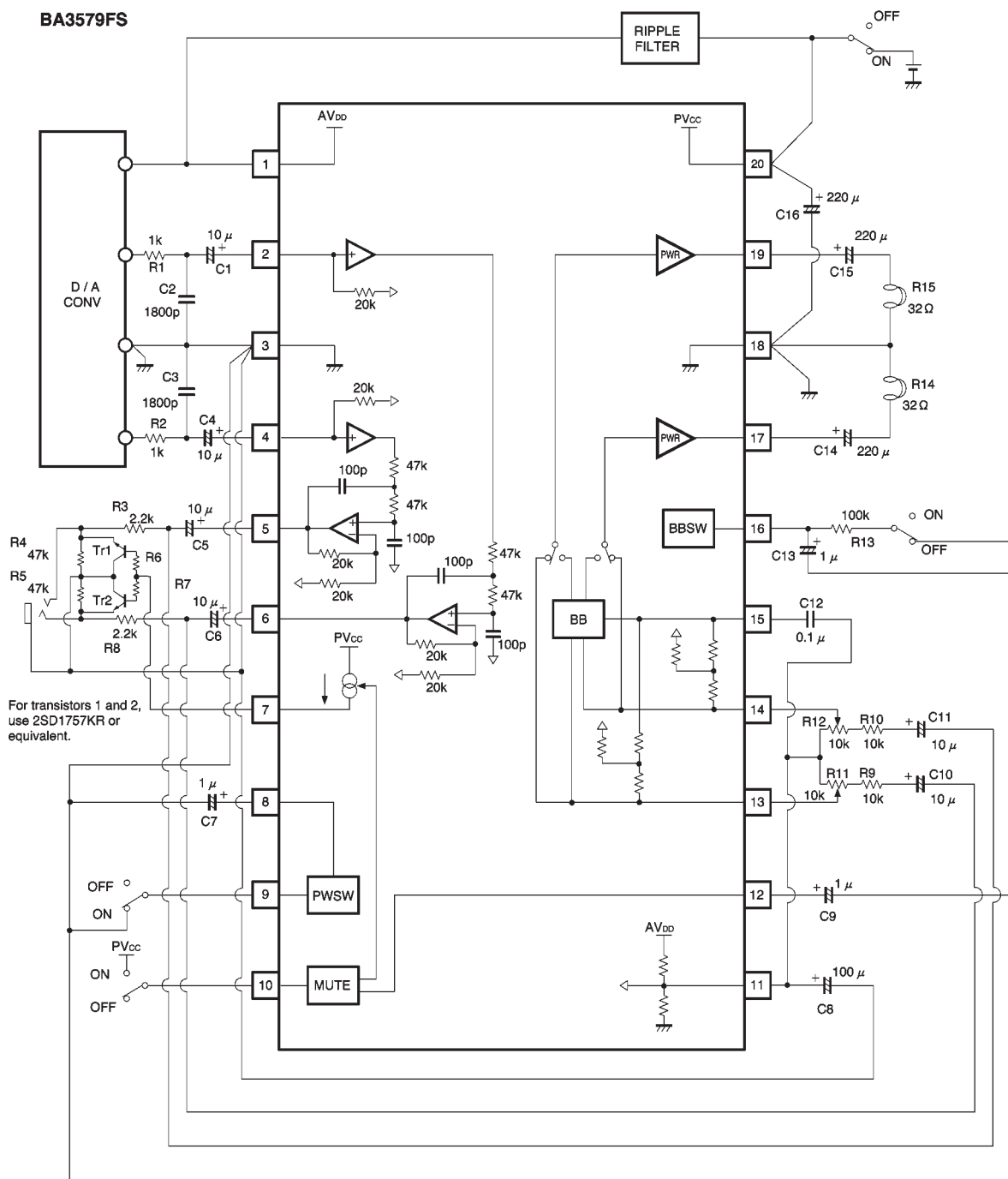
BA3578FS



Units:
 Resistance : Ω ($\pm 5\%$)
 Capacitance (film) : F ($\pm 10\%$)
 Capacitance (electrolytic): F ($\pm 20\%$)

Fig.3

BA3579FS



Units:
 Resistance : Ω ($\pm 5\%$)
 Capacitance (film) : F ($\pm 10\%$)
 Capacitance (electrolytic): F ($\pm 20\%$)

Fig.4

● Circuit operation

(1) By operating the BA3578FS and BA3579FS according to the timing chart shown in Fig. 5, it is possible to suppress generation of "pop" noise in the headphone output.

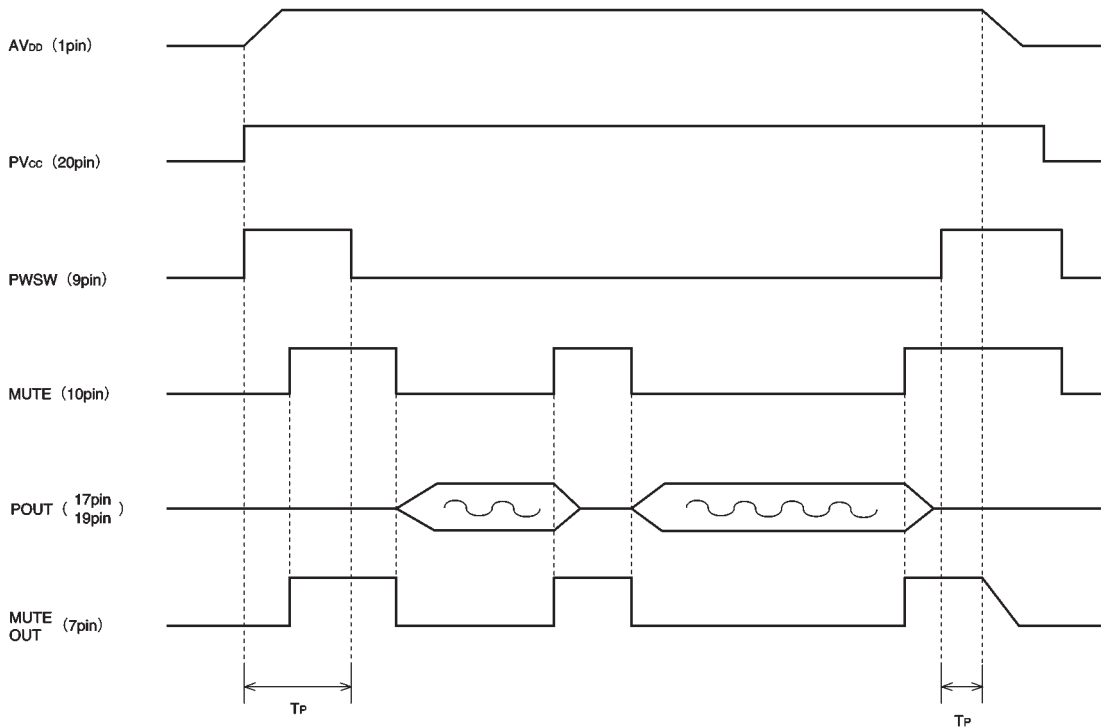


Fig.5 Timing chart

T_P 100msec.

(2) The voltage of the BIAS pin (pin 11) for the BA3578FS and BA3579FS is the voltage divided from the AVDD pin (pin 1). There is no current carrying capacity, so do not use it as an operating point for external circuits.

●Electrical characteristic curves

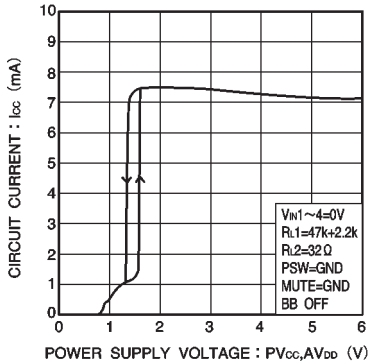


Fig.6 Circuit current vs. power supply voltage

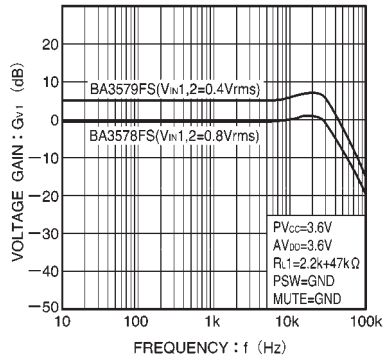


Fig.7 Voltage gain vs. power supply voltage (line-out)

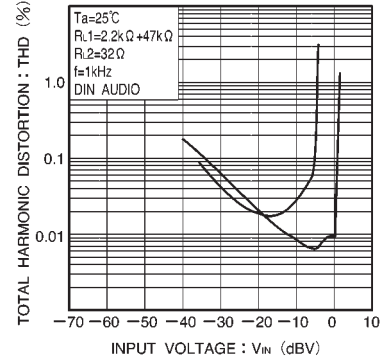


Fig.8 Total harmonic distortion vs. input voltage (line-out)

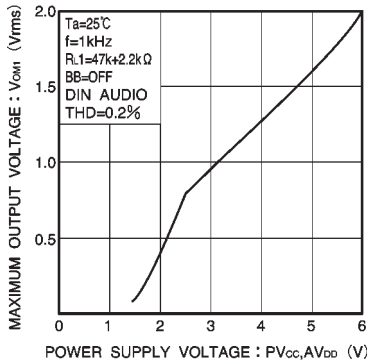


Fig.9 Maximum output voltage vs. power supply voltage (line-out)

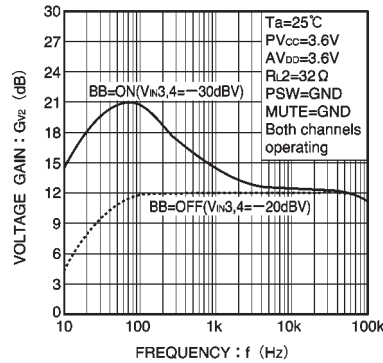


Fig.10 Voltage gain vs. frequency characteristics (headphone-out)

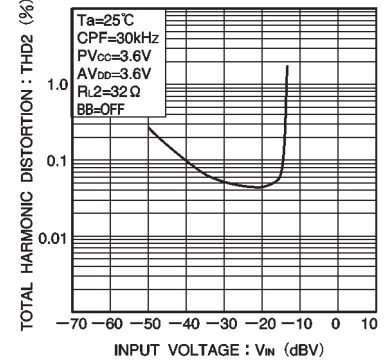


Fig.11 Total harmonic distortion vs. input voltage (headphone-out)

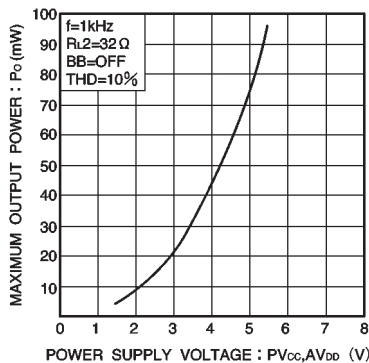
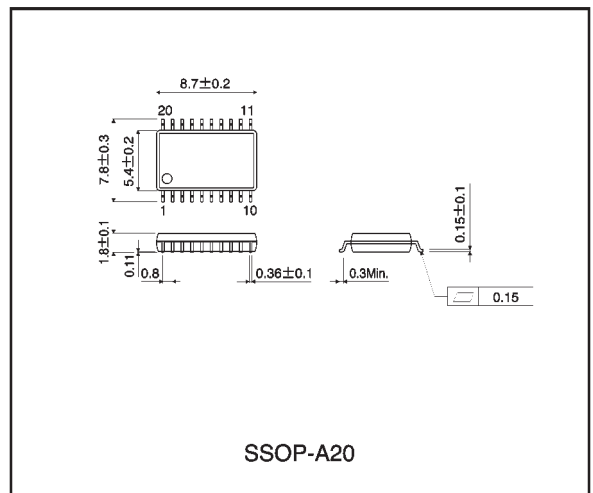


Fig.12 Maximum output voltage vs. power supply voltage (headphone-out)

●External dimensions (Unit: mm)



SSOP-A20

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